



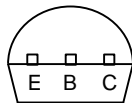
Micro Commercial Components  
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# 2N5551

## Features

- This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.

Pin Configuration  
Bottom View



## NPN General Purpose Amplifier Transistor

## Maximum Ratings

Symbol	Rating	Rating	Unit
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current	600	mA
$P_C$	Collector Power Dissipation	625	mW
$T_J$	Operating Junction Temperature	-55 to +150	$^{\circ}C$
$T_{STG}$	Storage Temperature	-55 to +150	$^{\circ}C$

## Electrical Characteristics @ 25 $^{\circ}C$ Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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### OFF CHARACTERISTICS

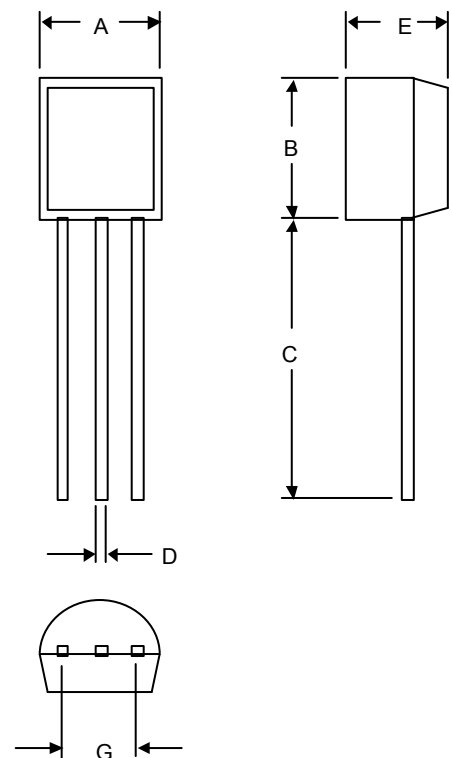
$V_{(BR)CEO}$	Collector-Emitter Voltage* ( $I_C=1.0mA$ , $I_B=0$ )	160	---	Vdc
$V_{(BR)CBO}$	Collector-Base Voltage ( $I_C=100\mu A$ , $I_E=0$ )	180	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Voltage ( $I_E=10\mu A$ , $I_C=0$ )	6.0	---	Vdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB}=35V$ , $I_E=0$ ) ( $V_{CB}=120V$ , $I_E=0$ , $T_A=100^{\circ}C$ )	---	50	nAdc uAdc
$I_{EBO}$	Emitter Cutoff Current ( $V_{EB}=5.0V$ , $I_C=0$ )	---	50	nAdc

### ON CHARACTERISTICS

$h_{FE}$	DC Current gain ( $I_C=1.0mA$ , $V_{CE}=5.0V$ ) ( $I_C=10mA$ , $V_{CE}=5.0V$ ) ( $I_C=50mA$ , $V_{CE}=5.0V$ )	80	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=50mA$ , $I_B=5.0mA$ )	---	0.5	Vdc
$V_{BE(sat)}$	Base- Emitter Voltage ( $I_B=5.0mA$ , $I_C=50mA$ )	---	1.0	Vdc

\* Pulse Test: Pulse Width<300us, Duty Cycle<2.0%

## TO-92



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	

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## ON CHARACTERISTICS

$f_T$	Transistor Frequency ( $V_{CE}=10Vdc, I_C=10mA$ )	100	300	MHz
$C_{ob}$	Collector Output Capacitance ( $V_{CB}=10Vdc, I_E=0, f=1.0MHz$ )	---	6.0	pF
$C_{ibo}$	Input Capacitance ( $V_{CE}=10Vdc, I_C=0, f=1.0MHz$ )	---	20	pF